



# **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

- · High Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 400V(Min)
- · High Switching Speed
- · High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

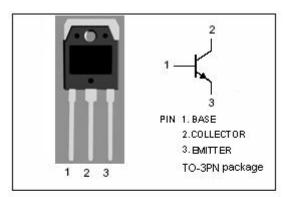


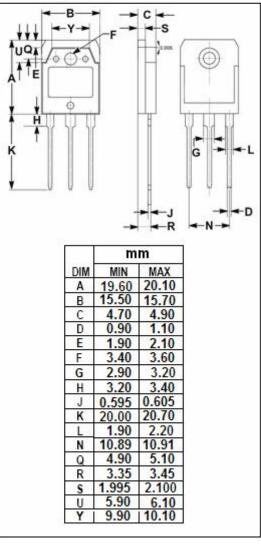
## **APPLICATIONS**

 Designed for switching regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V	
V <sub>EBO</sub>	Emitter-Base voltage	10	V	
Ic	Collector Current-Continuous	10	А	
Ісм	Collector Current-Peak(Pulse)	20	А	
I <sub>B</sub>	Base Current-Continuous	4	А	
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25℃	80	W	
Тл	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	







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2SC4138

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 25mA ; I <sub>B</sub> = 0	400			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.2A			0.5	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.2A			1.3	V			
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 500V ; I <sub>E</sub> = 0			0.1	mA			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 10V; I <sub>C</sub> = 0			0.1	mA			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 6A ; V <sub>CE</sub> = 4V	10		30				
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V; f <sub>test</sub> =1.0MHz		85		pF			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>E</sub> = -0.7A ; V <sub>CE</sub> = 12V		10		MHz			
Switching Times									
t <sub>on</sub>	Turn-on Time				1.0	μS			
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 6A,I <sub>B1</sub> = 0.6A; I <sub>B2</sub> = -1.2A R <sub>L</sub> = 33.3 Ω; V <sub>CC</sub> = 200V			3.0	μS			
t <sub>f</sub>	Fall Time				0.5	μs			

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